

*“On the evolution of strain and electrical properties in as-grown and annealed Si:P epitaxial films for source-drain stressor applications”*. Dhayalan SK, Kujala J, Slotte J, Pourtois G, Simoen E, Rosseel E, Hikavy A, Shimura Y, Loo R, Vandervorst W, ECS journal of solid state science and technology 7, P228 (2018). <http://doi.org/10.1149/2.0071805JSS>